

FORMATION OF $n^+ - n$
JUNCTIONS AT A STRESSED
INTERFACE QUANTUM DOT-MATRIX

R.M. Peleshchak, I.Ya. Bachynsky

Ivan Franko Drohobych State Pedagogical University
(24, Ivan Franko Str., Drohobych 82100, Ukraine;
e-mail: slajider@rambler.ru)

S u m m a r y

The theory of the formation of $n^+ - n$ junctions in stressed nanoheterosystems with quantum dots (QDs) has been developed in the framework of the self-consistent electron-deformation model. An electric double layer, i.e. an $n^+ - n$ junction, has been shown to emerge at the QD-matrix stressed interface.